

ABSTRACT

A method of fabricating a semiconductor device characterized in that the method includes the steps of forming basic structures of unit FETs on each of 'm' active layer regions more than the number of designed unit FETs and determining the number 'n' of desired basic structures on the basis of a drain current value of the semiconductor device predicted from a measured value of the drain current characteristics of one of the basic structures. The contact holes for electrical connections to electrodes of each of the unit FETs are formed for only the regions on 'n' basic structures in an inter-layer insulating film. In this manner, there is provided a method of fabricating a semiconductor device, the method being capable of improving degraded characteristics after the characteristics of TEG-FET have been measured.